

40. (Once Amended) The embedded electroconductive layer according to claim 3, wherein said barrier layer is composed of WN_x , where x is a variable such that $0 \leq x \leq 1$.

41. (Once Amended) The embedded electroconductive layer according to claim 3, wherein said barrier layer is composed of TaN_x , where x is a variable such that $0 \leq x \leq 1$.

42. (Once Amended) The embedded electroconductive layer according to claim 3, wherein said barrier layer is composed of amorphous $TiSiN$.

43. (Once Amended) The embedded electroconductive layer according to claim 3, wherein said barrier layer is composed of Al_2O_3 .

REMARKS

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached Appendix is captioned "**Version with markings to show changes made.**"

With this Supplemental Amendment, Applicant is amending new Claims 40-43 to correct for the antecedent basis problems that arose from Claims 40-43 as originally

presented in original Amendment C. Applicant respectfully requests that the Examiner consider newly amended Claims 40-43 along with the other claims and arguments presented in original Amendment C.

For the above reasons in this Supplemental Amendment C, as well as for the reasons presented in original Amendment C, Applicant requests reconsideration and allowance of the claimed invention. Should the Examiner be of the opinion that a telephone conference would aid in the prosecution of the application, or that outstanding issues exist, the Examiner is invited to contact the undersigned.

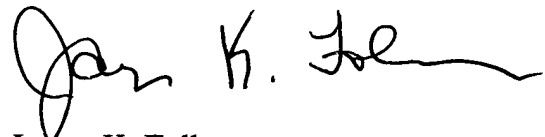
Respectfully submitted,

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June 13, 2002

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VERSION WITH MARKINGS TO SHOW CHANGES MADE**In the Claims:**

Claims 40-43 have been amended as follows:

40. (Once Amended) The embedded electroconductive layer according to claim 3, wherein said barrier layer ~~first material~~ is composed of WN_x , where x is a variable such that $0 \leq x \leq 1$.

41. (Once Amended) The embedded electroconductive layer according to claim 3, wherein said barrier layer ~~first material~~ is composed of TaN_x , where x is a variable such that $0 \leq x \leq 1$.

42. (Once Amended) The embedded electroconductive layer according to claim 3, wherein said ~~first material~~ barrier layer is composed of amorphous $TiSiN$.

43. (Once Amended) The embedded electroconductive layer according to claim 3, wherein said barrier layer ~~first material~~ is composed of Al_2O_3 .